



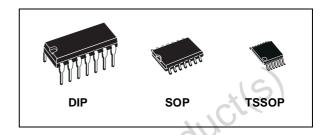
# **QUAD 2-INPUT OR GATE**

- HIGH SPEED:
  - $t_{PD}$  = 8ns (TYP.) at  $V_{CC}$  = 6V
- LOW POWER DISSIPATION:  $I_{CC} = 1\mu A(MAX.)$  at  $T_A=25^{\circ}C$
- HIGH NOISE IMMUNITY: V<sub>NIH</sub> = V<sub>NIL</sub> = 28 % V<sub>CC</sub> (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I<sub>OH</sub>| = I<sub>OL</sub> = 4mA (MIN)
- BALANCED PROPAGATION DELAYS: t<sub>PLH</sub> ≅ t<sub>PHL</sub>
- WIDE OPERATING VOLTAGE RANGE: V<sub>CC</sub> (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 32



The M74HC32 is an high speed CMOS QUAD 2-INPUT OR GATE fabricated with silicon gate  $\mbox{C}^2\mbox{MOS}$  technology.

The internal circuit is composed of 2 stages including buffer output, which enables high noise immunity and stable output.



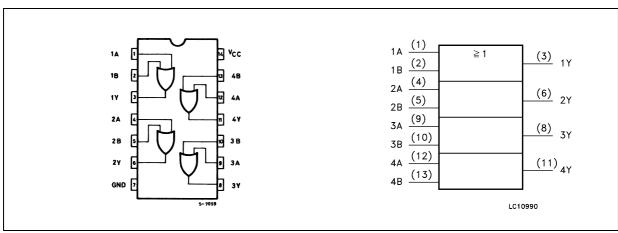
#### **ORDER CODES**

PACKAGE	TUBE	T & R
DIP	M74HC32B1R	
SOP	M74HC32M1R	M74HC32RM13TR
TSSOP		M74HC32TTR

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

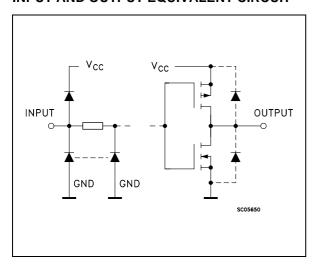
### PIN CONNECTION AND IEC LOGIC SYMBOLS

;olete Pro



July 2001 1/8

#### INPUT AND OUTPUT EQUIVALENT CIRCUIT



#### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

### **TRUTH TABLE**

Α	В	Y
L	L	4
L	Н	H
Н	L	Н
Н	Н	Н

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
$P_{D}$	Power Dissipation	500(*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied
(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V <sub>CC</sub>	V
V <sub>O</sub>	Output Voltage		0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	V <sub>CC</sub> = 2.0V	0 to 1000	ns
$t_r$ , $t_f$		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

#### **DC SPECIFICATIONS**

		Т	est Condition				Value				
Symbol	mbol Parameter		V <sub>CC</sub>		T <sub>A</sub> = 25°C -40 t			to 85°C   -55 to 125°C			Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		6.0		4.2			4.2		4.2		
$V_{IL}$	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0				1.8		1.8		1.8	
V <sub>OH</sub>	High Level Output	2.0	I <sub>O</sub> =-20 μA	1.9	2.0		1.9		1.9	16	\
	Voltage	4.5	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		1
		6.0	I <sub>O</sub> =-20 μA	5.9	6.0		5.9	1	5.9		V
		4.5	I <sub>O</sub> =-4.0 mA	4.18	4.31		4.13	$\sim$ 0	4.10		
		6.0	I <sub>O</sub> =-5.2 mA	5.68	5.8		5.63	O	5.60		
V <sub>OL</sub>	Low Level Output	2.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		6.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =4.0 mA	C	0.17	0.26		0.33		0.40	
		6.0	I <sub>O</sub> =5.2 mA	0	0.18	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ
I <sub>CC</sub>	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			1		10		20	μА

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ns}$ )

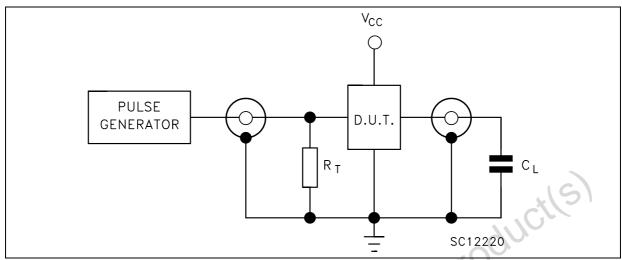
	240	J 1	Test Condition		Value						
Symbol	Symbol Parameter		Parameter V <sub>CC</sub>		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C	
	76	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t <sub>TLH</sub> t <sub>THL</sub>	Output Transition	2.0			30	75		95		110	
60	Time	4.5			8	15		19		22	ns
03		6.0			7	13		16		19	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay	2.0			24	75		95		110	
	Time	4.5			9	15		19		22	ns
		6.0			8	13		16		19	

#### **CAPACITIVE CHARACTERISTICS**

	Test Condition		Value								
Symbol	·		/cc		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C	
			(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance	5.0			5	10		10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	5.0			21						pF

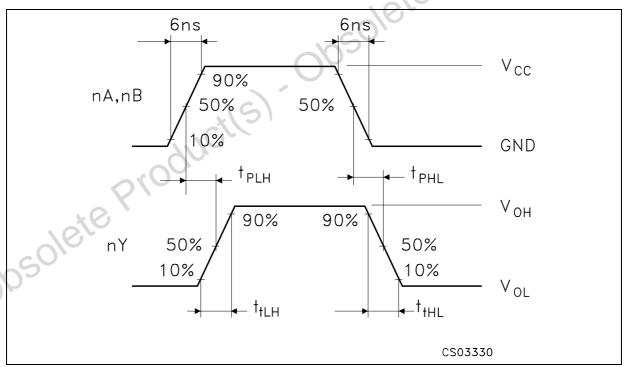
<sup>1)</sup> C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> x V<sub>CC</sub> x f<sub>IN</sub> + I<sub>CC</sub>/4 (per gate)

#### **TEST CIRCUIT**



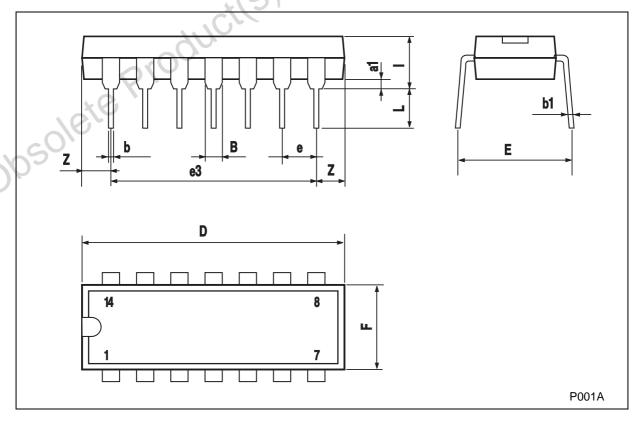
 $C_L$  = 50pF or equivalent (includes jig and probe capacitance)  $R_T$  =  $Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

### WAVEFORM: PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)



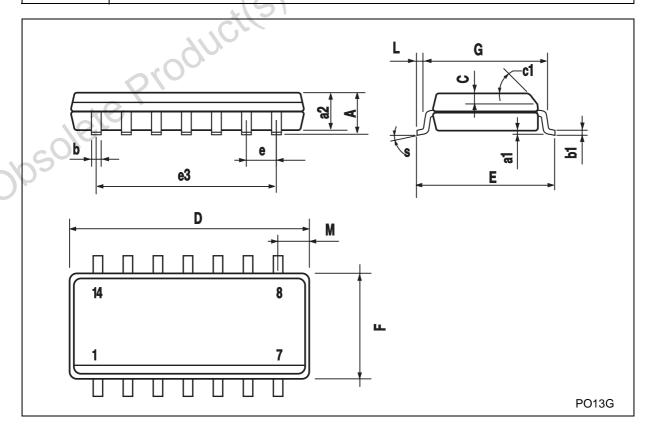
# **Plastic DIP-14 MECHANICAL DATA**

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	16
D			20		.(	0.787
E		8.5			0.335	
е		2.54			0.100	
e3		15.24		× (2)	0.600	
F			7.1	76/		0.280
I			5.1	0.		0.201
L		3.3	Oh		0.130	
Z	1.27		2.54	0.050		0.100



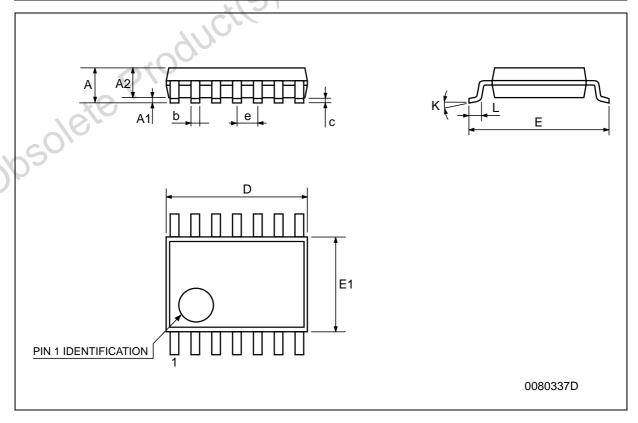
# **SO-14 MECHANICAL DATA**

DIM		mm.			inch		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α			1.75			0.068	
a1	0.1		0.2	0.003		0.007	
a2			1.65			0.064	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019	1(5)	
c1			45° (	typ.)	.(		
D	8.55		8.75	0.336	40	0.344	
E	5.8		6.2	0.228	400	0.244	
е		1.27			0.050		
e3		7.62		28	0.300		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.68			0.026	
S			8° (m	nax.)			



# **TSSOP14 MECHANICAL DATA**

DIM.		mm.		inch					
DIWI.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.			
А			1.2			0.047			
A1	0.05		0.15	0.002	0.004	0.006			
A2	0.8	1	1.05	0.031	0.039	0.041			
b	0.19		0.30	0.007		0.012			
С	0.09		0.20	0.004	AU!	0.0089			
D	4.9	5	5.1	0.193	0.197	0.201			
E	6.2	6.4	6.6	0.244	0.252	0.260			
E1	4.3	4.4	4.48	0.169	0.173	0.176			
е		0.65 BSC	- 100	0,	0.0256 BSC				
К	0°		8°	0°		8°			
L	0.45	0.60	0.75	0.018	0.024	0.030			





Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco Singapore - Spain - Sweden - Switzerland - United Kingdom © http://www.st.com